	Application No.	Application No. Applicant(s)	
Notice of Allowability	10/604,406	HSU ET AL.	
	Examin r	Art Unit	
	Tu-Tu Ho	2818	
The MAILING DATE of this communication All claims being allowable, PROSECUTION ON THE MERIT herewith (or previously mailed), a Notice of Allowance (PTOL NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATEN of the Office or upon petition by the applicant. See 37 CFR 1	S IS (OR REMAINS) CLOSED 85) or other appropriate comm IT RIGHTS. This application is	in this application. If not include nunication will be mailed in due	ded e course. THIS
 This communication is responsive to Paper filed 18 July 2. ☐ The allowed claim(s) is/are 1-9. The drawings filed on 18 July 2003 are accepted by the Acknowledgment is made of a claim for foreign priority a) ☐ All b) ☐ Some* c) ☐ None of the: Certified copies of the priority documents Copies of the certified copies of the priority documents 	ne Examiner. y under 35 U.S.C. § 119(a)-(d) have been received. have been received in Applicat y documents have been receiv	ion No	ation from the
International Bureau (PCT Rule 17.2(a * Certified copies not received: 5. Acknowledgment is made of a claim for domestic prior (a) The translation of the foreign language provision 6. Acknowledgment is made of a claim for domestic prior Applicant has THREE MONTHS FROM THE "MAILING DATI below. Failure to timely comply will result in ABANDONMEN"	ity under 35 U.S.C. § 119(e) (to nal application has been receiv ity under 35 U.S.C. §§ 120 and E" of this communication to file	ed. I/or 121. a reply complying with the req	
7. A SUBSTITUTE OATH OR DECLARATION must be s INFORMAL PATENT APPLICATION (PTO-152) which gives			NOTICE OF
8. CORRECTED DRAWINGS must be submitted. (a) including changes required by the Notice of Draft 1) hereto or 2) to Paper No. (b) including changes required by the proposed draw (c) including changes required by the attached Example.	ring correction filed, wh	ich has been approved by the	
identifying indicia such as the application number (see 37 C each sheet.	FR 1.84(c)) should be written on	the drawings in the front (not th	ie back) of
9. DEPOSIT OF and/or INFORMATION about the d attached Examiner's comment regarding REQUIREMENT FO			Note the
Attachment(s)			
 1⊠ Notice of References Cited (PTO-892) 3☐ Notice of Draftperson's Patent Drawing Review (PTO-94 5☐ Information Disclosure Statements (PTO-1449), Paper N 7☐ Examiner's Comment Regarding Requirement for Depos of Biological Material 	8) 4☐ Intervie lo 6☐ Examir it 8⊠ Examir 9☐ Other	of Informal Patent Application ew Summary (PTO-413), Pape ner's Amendment/Comment ner's Statement of Reasons for	er No
	David Neims Gupervisory Patent Examiner Technology Center 2800		

DETAILED ACTION

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Allowable Subject Matter

1. Claims 1-9 are allowable over the prior art of record.

The following is an examiner's statement of reasons for allowance: The prior art of record fails to teach or render obvious a flash memory with all limitations as recited in claim 1.

Specifically, the prior art of record, in disclosing flash memory systems with global and local bit lines, fails to disclose that the source of each memory cell consists of a first doped region of the first conductivity type and a second doped region of the second conductivity type that surrounds the first doped region and is short-circuited with the first doped region.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

- 2. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Copies of the references are not being furnished with this Office Action per MPEP § 707.05(a).
- a. U.S. Patent 6,038,170 to Shiba discloses a semiconductor integrated circuit device including a plurality of divided sub-bit lines wherein source and drain regions are formed in doped wells.

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b. U.S. Patent 6,172,397 to Oonakado et al. discloses a non-volatile semiconductor

memory device having a p type source region and a p type drain region being formed in a surface

of an n well and having a data program means for injecting electrons from within the drain

region to the floating gate charge storage electrode by hot electron injection induced by a band-

to-band tunnel current.

3. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Tu-Tu Ho whose telephone number is (703) 305-0086. The

examiner can normally be reached on 6:30 am - 5:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, DAVID NELMS can be reached on (703) 308-4910. The fax phone numbers for the

organization where this application or proceeding is assigned are (703) 872-9306 for regular

communications and (703) 872-9306 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is (703) 308-1782.

Tu-Tu Ho

October 23, 2003

Supervisory Patent Examinor

Technology Center 2800